

Title (en)
SEMICONDUCTOR SUBSTRATE

Title (de)
HALBLEITERSUBSTRAT

Title (fr)
SUBSTRAT SEMI-CONDUCTEUR

Publication
EP 3550591 A4 20200805 (EN)

Application
EP 17877266 A 20171128

Priority
• JP 2016231901 A 20161130
• JP 2017042694 W 20171128

Abstract (en)
[origin: EP3550591A1] A semiconductor wafer is provided, which has a buffer layer having a stacked structure in which first crystal layers formed of AlGa_N and second crystal layers formed of AlGa_N are repeatedly stacked, where when TEM observation of a cross-section of the buffer layer is performed at an observation region including one of the first crystal layers, HAADF-STEM intensity I(D) being a function of a depth D takes a local minimum value I_{min} at a depth D_{min} and takes a local maximum value I_{max} at a depth D_{max} (D_{max} > D_{min}), and a depth direction distance DD1 from a depth at which the I(D) takes an intermediate value I_{mid} of the I_{max} and the I_{min} to a depth at which the I(D) takes the I_{min} in a monotonous decrease region disposed shallower than the D_{min}, and a depth direction distance DD2 from a depth at which the I(D) takes the I_{min} to a depth at which the I(D) takes the I_{max} in a monotonous increase region disposed deeper than the D_{min} satisfy a condition that $DD1 \leq 0.3 \times DD2$.

IPC 8 full level
H01L 21/205 (2006.01); **C23C 16/30** (2006.01); **C23C 16/34** (2006.01); **G01N 23/04** (2018.01); **G01N 23/20058** (2018.01); **H01L 21/02** (2006.01); **H01L 21/338** (2006.01); **H01L 29/778** (2006.01); **H01L 29/812** (2006.01)

CPC (source: EP US)
C23C 16/30 (2013.01 - EP US); **C23C 16/34** (2013.01 - EP US); **H01L 21/02381** (2013.01 - EP US); **H01L 21/02458** (2013.01 - EP US); **H01L 21/02505** (2013.01 - EP US); **H01L 21/02507** (2013.01 - EP US); **H01L 21/0254** (2013.01 - EP US); **H01L 21/0262** (2013.01 - EP US); **H01L 29/2003** (2013.01 - US); **H01L 29/205** (2013.01 - US); **H01L 29/778** (2013.01 - EP US); **H01L 29/812** (2013.01 - EP US); **H01L 29/7786** (2013.01 - US)

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• See references of WO 2018101280A1

Designated contracting state (EPC)
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